IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A process for producing a light emitting device comprising the steps of:

forming an anode;

~~wiping/cleaning~~ wiping and cleaning the surface of the anode with a ~~wiping/cleaning~~ wiping and cleaning material~~.~~;

forming an organic compound layer on the anode after ~~wiping/cleaning~~ wiping and cleaning the surface of thereof; and

forming a cathode on the organic compound layer.

2. (Original) The process for producing the light emitting device according to claim 1, wherein the anode is composed of a transparent conductive film.

3. (Currently amended) The process for producing the light emitting device according to claim 1, wherein the surface is made flat by the ~~wiping/cleaning~~ wiping and cleaning.

4. (Currently amended) The process for producing the light emitting device according to claim 1, wherein the ~~wiping/cleaning~~ wiping and cleaning material is a PVA-based porous body.

5. (Currently amended) The process for producing the light emitting device according to claim 1, wherein the surface is ~~wiped/cleaned~~ wiped and cleaned with the ~~wiping/cleaning~~ wiping and cleaning material and a washing liquid.

6. (Currently amended) The process for producing the light emitting device according to claim 1, wherein the surface is scrubbed with the ~~wiping/cleaning~~ wiping and cleaning material.

7. (Currently amended) The process for producing the light emitting device according to claim 1, wherein when contact angle to the anode surface is smaller than 90° before the ~~wiping/cleaning~~ wiping and cleaning, the contact angle after the ~~wiping/cleaning~~ wiping and cleaning is larger than the contact angle before the ~~wiping/cleaning~~ wiping and cleaning and is smaller than 90°.

8. (Currently amended) A process for producing an active matrix type light emitting device comprising the steps of:

forming TFTs over a substrate;

forming a first insulating film comprising organic resin material over the TFTs;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming a transparent conductive film on the second insulating film; and

~~wiping/cleaning~~ wiping and cleaning the surface of the transparent conductive film with a ~~wiping/cleaning~~ wiping and cleaning material.

9. (Previously presented) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming an anode on the second insulating film; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

10. (Previously presented) The process for producing the active matrix type light emitting device according to claim 9, wherein the surface of the anode is made flat by the wiping and cleaning material.

11. (Previously presented) The process for producing the active matrix type light emitting device according to claim 9, wherein the organic resin material is selected form the group consisting of polyacrylate, polyimide and polyamide.

12. (Previously presented) The process for producing the active matrix type light emitting device according to claim 9, wherein the inorganic insulating material is selected

from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide.

13. (Previously presented) The process for producing the active matrix type light emitting device according to claim 9, wherein the wiping and cleaning material is a PVA-based porous body.

14. (Previously presented) The process for producing the active matrix type light emitting device according to claim 9, wherein the anode is wiped and cleaned with the wiping and cleaning material and a washing liquid.

15. (Previously presented) The process for producing the active matrix type light emitting device according to claim 9, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

16. (Previously presented) The process for producing the active matrix type light emitting device according to claim 9, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

17. (Currently amended) A process for producing a light emitting device comprising the steps of:

forming a transparent conductive film;

forming an insulating film comprising an organic resin material on the transparent conductive film; and

~~wiping/cleaning~~ wiping and cleaning the surface of the insulating film with a ~~wiping/cleaning~~ wiping and cleaning material.

18. (Currently amended) A process for producing a light emitting device comprising the steps of:

forming an anode;

forming an insulating film comprising an organic resin material on the anode; and

~~wiping/cleaning~~ wiping and cleaning the surface of the insulating film with a ~~wiping/cleaning~~ wiping and cleaning material.

19. (Currently amended) The process for producing the light emitting device according to claim 17, wherein the surface of the insulating film is made flat by the ~~wiping/cleaning~~ wiping and cleaning.

20. (Currently amended) The process for producing the light emitting device according to claim 17, wherein the ~~wiping/cleaning~~ wiping and cleaning material is a PVA-based porous body.

21. (Currently amended) The process for producing the light emitting device according to claim 17, wherein the surface of the insulating film is ~~wiped/cleaned~~ wiped and cleaned with the ~~wiping/cleaning~~ wiping and cleaning material and a washing liquid.

22. (Currently amended) The process for producing the light emitting device according to claim 17, wherein the surface of the insulating film is scrubbed with the ~~wiping/cleaning~~ wiping and cleaning material.

23. (Currently amended) The process for producing the light emitting device according to claim 17, wherein when contact angle to the insulating film is smaller than 90° before the ~~wiping/cleaning~~ wiping and cleaning, the contact angle after the ~~wiping/cleaning~~ wiping and cleaning is larger than the contact angle before the ~~wiping/cleaning~~ wiping and cleaning and is smaller than 90°.

24. (Original) The process for producing the light emitting device according to claim 17, wherein the insulating film is formed to have a film thickness of 1 to 50 nm.

25. (Original) The process for producing the light emitting device according to claim 17, wherein the insulating film comprises a material selected from the group consisting of polyacrylate, polyimide or polyamide.

26. (Currently amended) A process for producing an active matrix type light emitting device comprising the steps of:

forming TFTs over a substrate;

forming a first insulating film comprising an organic resin material over the TFTs;

forming a second insulating film comprising an inorganic insulating material on the first insulating film;

forming a transparent conductive film on the second insulating film;

forming a third insulating film comprising an organic resin material on the transparent conductive film; and

~~wiping/cleaning~~ wiping and cleaning the surface of the third insulating film with a ~~wiping/cleaning~~ wiping and cleaning material.

27. (Currently amended) A process for producing an active matrix type light emitting device comprising the steps of:

forming TFTs over a substrate;

forming a first insulating film comprising an organic resin material over the TFTs;

forming a second insulating film comprising an inorganic insulating material on the first insulating film;

forming an anode on the second insulating film;

forming a third insulating film comprising an organic resin material on the anode; and

~~wiping/cleaning~~ wiping and cleaning the surface of the third insulating film with a ~~wiping/cleaning~~ wiping and cleaning material.

28. (Currently amended) The process for producing the light emitting device according to claim 26, wherein the surface of the third insulating film is made flat by the ~~wiping/cleaning~~ wiping and cleaning.

29. (Original) The process for producing the light emitting device according to claim 26, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

30. (Currently amended) The process for producing the light emitting device according to claim 26, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide~~, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride~~.

31. (Currently amended) The process for producing the light emitting device according to claim 26, wherein the ~~wiping/cleaning~~ wiping and cleaning material is a PVA-based porous body.

32. (Currently amended) The process for producing the light emitting device according to claim 26, wherein the transparent conductive film is ~~wiped/cleaned~~ wiped and cleaned with the ~~wiping/cleaning~~ wiping and cleaning material and a washing liquid.

33. (Currently amended) The process for producing the light emitting device according to claim 26, wherein the surface of the third insulating film is scrubbed with the ~~wiping/cleaning~~ wiping and cleaning material.

34. (Original) The process for producing the light emitting device according to claim 26, wherein the third insulating film is formed to have a film thickness of 1 to 50 nm.

35. (Original) The process for producing the light emitting device according to claim 26, wherein the third insulating film is made of polyacrylate, polyimide or polyamide.

36. (Currently amended) The process for producing the light emitting device according to claim 26, wherein when contact angle to the surface of the third insulating film is smaller than 90° before the ~~wiping/cleaning~~ wiping and cleaning, the contact angle after the ~~wiping/cleaning~~ wiping and cleaning is larger than the contact angle before the ~~wiping/cleaning~~ wiping and cleaning and is smaller than 90°.

37. (Currently amended) The process for producing the light emitting device according to claim 26, wherein the TFT is manufactured by following steps:

first step of forming a semiconductor layer over the substrate;

second step of forming an insulating film on the semiconductor layer;

third step of forming a conductive layer on the insulating film;

fourth step of selectively etching the conductive layer to form a first conductive layer having a first tapered shape;

fifth step of introducing an impurity element into the semiconductor layer;

sixth step of selectively etching the first tapered shape; and

seventh step of introducing ~~the e first conductive layer to form a second conductive layer having a second~~ the impurity element into the semiconductor layer,

wherein the concentration of the impurity element introduced in the seventh step is lower than that introduced in the fifth step.

38. (Previously presented) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming a transparent conductive film formed on the second insulating film;

patterning the transparent conductive film to form an anode; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

39. (Previously presented) The process for producing the active matrix type light emitting device according to claim 38, wherein the surface of the anode is made flat by the wiping and cleaning material.

40. (Previously presented) The process for producing the active matrix type light emitting device according to claim 38, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

41. (Currently amended) The process for producing the active matrix type light emitting device according to claim 38, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide~~, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride~~.

42. (Previously presented) The process for producing the active matrix type light emitting device according to claim 38, wherein the wiping and cleaning material is a PVA-based porous body.

43. (Previously presented) The process for producing the active matrix type light emitting device according to claim 38, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

44. (Previously presented) The process for producing the active matrix type light emitting device according to claim 38, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

45. (Previously presented) The process for producing the active matrix type light emitting device according to claim 38, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

46. (Previously presented) A process for producing an active matrix light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic material on the first insulating film;

forming an electrode connected to the thin film transistor on the second insulating film;

forming an anode formed on the electrode and the second insulating film; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

47. (Previously presented) The process for producing the active matrix type light emitting device according to claim 46, wherein the surface of the anode is made flat by the wiping and cleaning material.

48. (Previously presented) The process for producing the active matrix type light emitting device according to claim 46, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

49. (Previously presented) The process for producing the active matrix type light emitting device according to claim 46, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide.

50. (Previously presented) The process for producing the active matrix type light emitting device according to claim 46, wherein the wiping and cleaning material is a PVA-based porous body.

51. (Previously presented) The process for producing the active matrix type light emitting device according to claim 46, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

52. (Previously presented) The process for producing the active matrix type light emitting device according to claim 46, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

53. (Previously presented) The process for producing the active matrix type light emitting device according to claim 46, wherein when contact angle to the surface of the

anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

54. (Previously presented) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming an anode on the second insulating film;

wiping and cleaning the surface of the anode with a wiping and cleaning material; and

forming an organic compound layer on the wiped and cleaned surface of the anode.

55. (Previously presented) The process for producing the active matrix type light emitting device according to claim 54, wherein the surface of the anode is made flat by the wiping and cleaning material.

56. (Previously presented) The process for producing the active matrix type light emitting device according to claim 54, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

57. (Previously presented) The process for producing the active matrix type light emitting device according to claim 54, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide.

58. (Previously presented) The process for producing the active matrix type light emitting device according to claim 54, wherein the wiping and cleaning material is a PVA-based porous body.

59. (Previously presented) The process for producing the active matrix type light emitting device according to claim 54, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

60. (Previously presented) The process for producing the active matrix type light emitting device according to claim 54, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

61. (Previously presented) The process for producing the active matrix type light emitting device according to claim 54, wherein when contact angle to the surface of the

anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

62. (Previously presented) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;

forming a second insulating film on the first insulating film;

forming an anode on the second insulating film; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

63. (Previously presented) The process for producing the active matrix type light emitting device according to claim 62, wherein the surface of the anode is made flat by the wiping and cleaning material.

64. (Previously presented) The process for producing the active matrix type light emitting device according to claim 62, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

65. (Previously presented) The process for producing the active matrix type light emitting device according to claim 62, wherein the inorganic insulating material is selected from

the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide.

66. (Previously presented) The process for producing the active matrix type light emitting device according to claim 62, wherein the wiping and cleaning material is a PVA-based porous body.

67. (Previously presented) The process for producing the active matrix type light emitting device according to claim 62, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

68. (Previously presented) The process for producing the active matrix type light emitting device according to claim 62, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

69. (Previously presented) The process for producing the active matrix type light emitting device according to claim 62, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

70. (Previously presented) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;

forming a second insulating film on the first insulating film;

forming an anode on the second insulating film;

wiping and cleaning the surface of the anode with a wiping and cleaning material; and

forming an organic compound layer on the wiped and cleaned surface of the anode.

71. (Previously presented) The process for producing the active matrix type light emitting device according to claim 70, wherein the surface of the anode is made flat by the wiping and cleaning material.

72. (Previously presented) The process for producing the active matrix type light emitting device according to claim 70, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

73. (Previously presented) The process for producing the active matrix type light emitting device according to claim 70, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide.

74. (Previously presented) The process for producing the active matrix type light emitting device according to claim 70, wherein the wiping and cleaning material is a PVA-based porous body.

75. (Previously presented) The process for producing the active matrix type light emitting device according to claim 70, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

76. (Previously presented) The process for producing the active matrix type light emitting device according to claim 70, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

77. (Previously presented) The process for producing the active matrix type light emitting device according to claim 70, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.